



UV-A Sensor

GUVV-T10GD-L

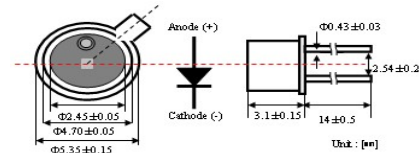


- Features**
- Indium Gallium Nitride Based Material
 - Schottky-type Photodiode
 - Photovoltaic Mode Operation
 - High Responsivity & Low Dark Current



- Applications**
- Full UV Band Monitoring
 - UV-A Lamp Monitoring
 - Sterilization Lamp Monitoring

Outline Diagrams and Dimensions



Absolute Maximum Ratings

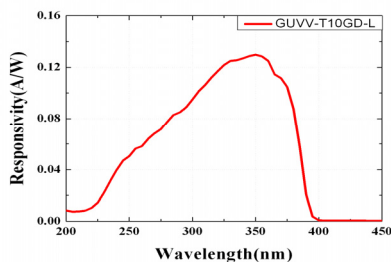
Parameter	Symbol	Min.	Max.	Unit	Remark
Storage Temperature	T_{st}	-40	90	°C	
Operating Temperature	T_{op}	-30	85	°C	
Reverse Voltage	$V_{r, max.}$		2	V	
Forward Current	$I_{f, max.}$		1	mA	
Optical Source Power Range	P_{opt}	0.01	100,000	$\mu W/cm^2$	UVA Lamp
Soldering Temperature	T_{sol}		260	°C	within 10 sec.

※Notice: apply to us in the case that Optical Source Power is over 100,000 $\mu W/cm^2$.

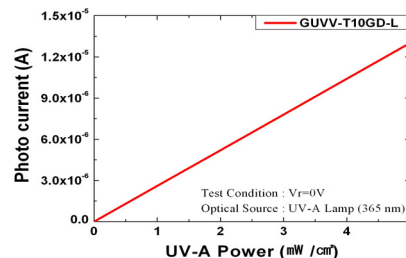
Characteristics (at 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Dark Current	I_d			20	nA	$V_r = 0.1 V$
Photo Current	I_{ph}		2.6		μA	UVA Lamp, 1mW/cm ²
Temperature Coefficient	I_{tc}		0.1		%/°C	UVA Lamp
Responsivity	R		0.13		A/W	$\lambda = 350 nm, V_r = 0 V$
Spectral Detection Range	λ	230		395	nm	10% of R
Active area			1.536		mm ²	

Responsivity Curve



Photocurrent along UV Power



Caution

ESD can damage the device hence please avoid ESD.

Insulate the cap of TO-CAN or it can cause malfunction of the device.